

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	2Ω@10V	100mA
	2.5Ω@4.5V	

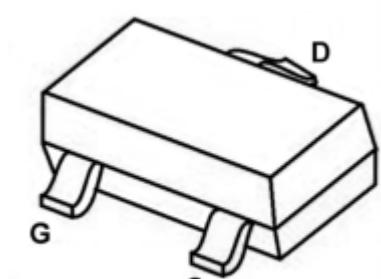
## Feature

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel
- ESD Protected

## Application

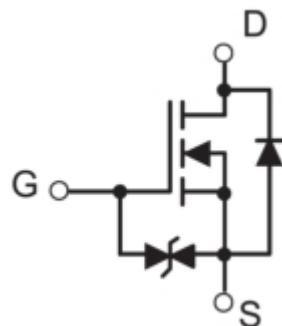
- Interfacing , Switching

## Package

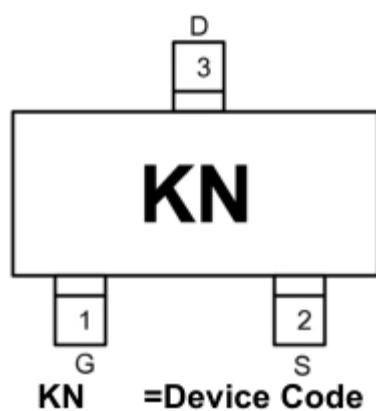


SOT-523

## Circuit diagram



## Marking



## Absolute maximum ratings

( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	100	mA
Power Dissipation	$P_D$	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	$^\circ\text{C}$



ZL MOSFET

2SK3019

## Electrical characteristics

(T<sub>A</sub>=25°C, unless otherwise noted)

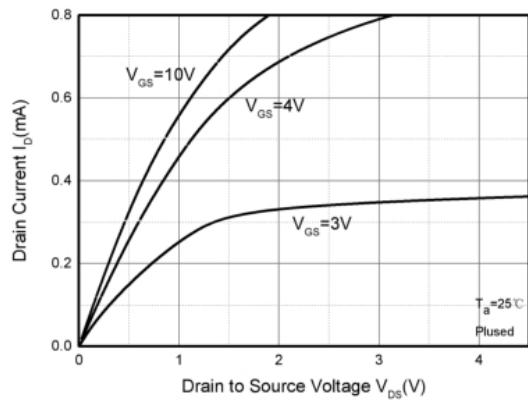
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±5	μA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.7	1	1.45	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 200mA V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA		2	5	Ω
				2.5	8	
<b>Dynamic characteristics</b>						
Input Capacitance1)	C <sub>iss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f=1MHZ		27		pF
Output Capacitance1)	C <sub>oss</sub>			13		
Reverse Transfer Capacitance1)	C <sub>rss</sub>			6		
<b>Switching Characteristics</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =30 V,I <sub>D</sub> =0.29A, V <sub>GEN</sub> =10V,R <sub>G</sub> =6Ω			5	ns
Rise time	tr				18	
Turn-off delay time	t <sub>d(off)</sub>				36	
Fall time	tf				14	
<b>Source-Drain Diode Characteristics</b>						
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> =500mA	0.5		1.4	V

### Notes:

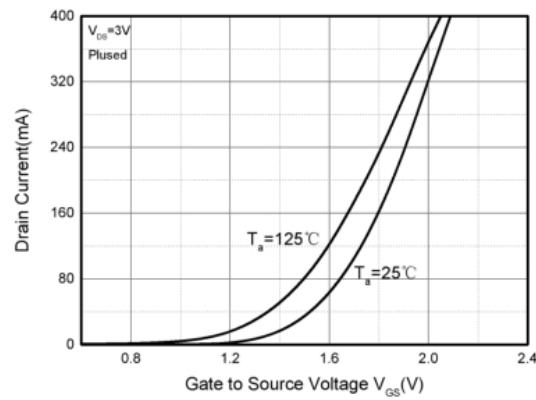
1.Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%.

2.These parameters have no way to verify.

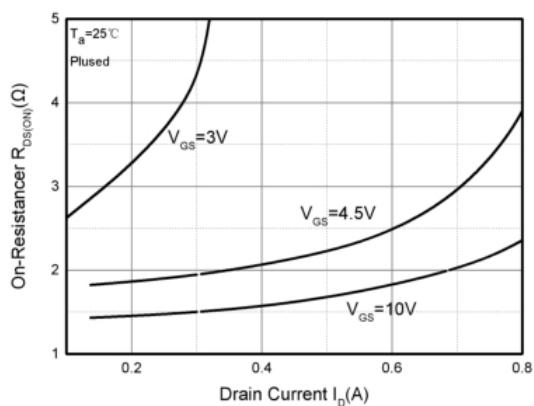
## Typical Characteristics



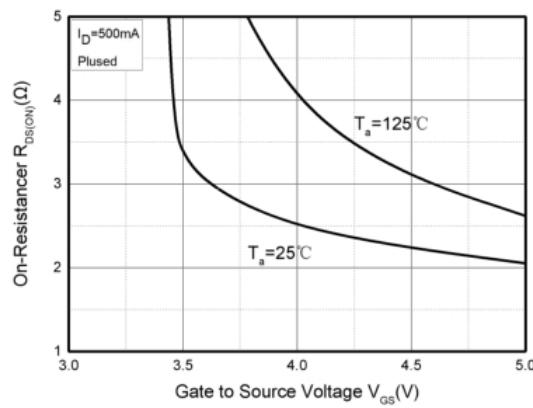
Output Characteristics



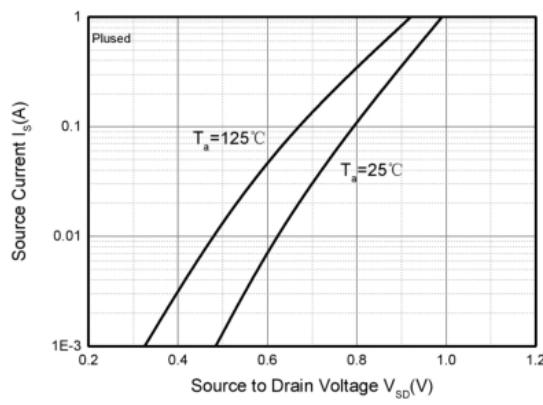
Transfer Characteristics



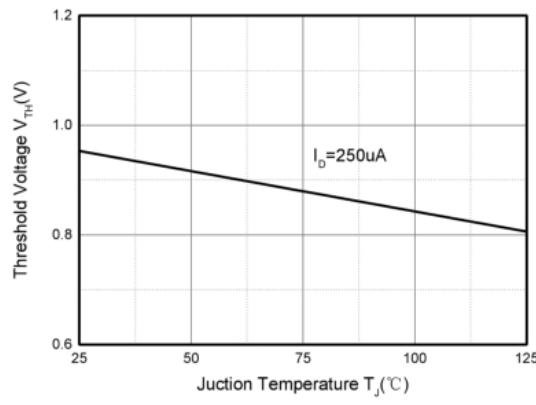
RDS(ON) — ID



RDS(ON) — VGS

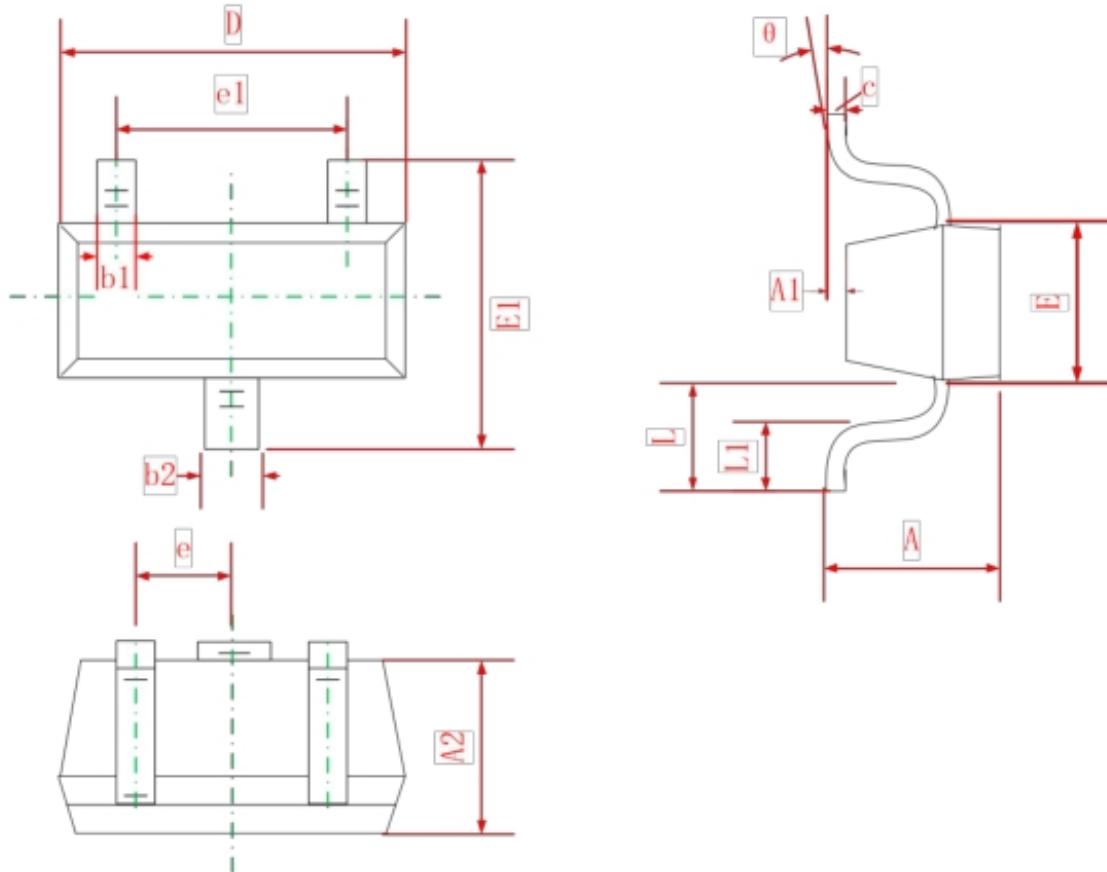


IS — VSD



Threshold Voltage

## SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°